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).	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
	01/23/2004	Kuniaki Nakano	KOY-15	7580
7590	06/06/2005		EXAM	INER
MUSERLIAN, LUCAS AND MERCANTI, LLP			SCHILLING, RICHARD L	
	SOUTH		ARTHNIT	PAPER NUMBER
15TH FLOOR NEW YORK, NY 10016			1752	TAI EK NOMBER
	7590 JAN, LU LAVENUE DOR	01/23/2004 7590 06/06/2005 JIAN, LUCAS AND MERCA AVENUE SOUTH OOR	01/23/2004 Kuniaki Nakano 7590 06/06/2005 JAN, LUCAS AND MERCANTI, LLP A VENUE SOUTH OOR	01/23/2004 Kuniaki Nakano KOY-15 7590 06/06/2005 EXAM JIAN, LUCAS AND MERCANTI, LLP SCHILLING, AVENUE SOUTH OOR ART UNIT

DATE MAILED: 06/06/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	/^
Office Action Summary	10/763,369	NAKANO ET AL.	
omoc Action Cummary	Examiner	Art Unit	
The MAILING DATE of this communication a	Richard L. Schilling	ith the correspondence address	
Period for Reply	ppour o on the outer on out	con coponacino dadi coc	
A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a r - If NO period for reply is specified above, the maximum statutory peri - Failure to reply within the set or extended period for reply will, by star Any reply received by the Office later than three months after the may earned patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no event, however, may a reply within the statutory minimum of thiod will apply and will expire SIX (6) MO tute, cause the application to become A	reply be timely filed rty (30) days will be considered timely. NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on			
2a) ☐ This action is FINAL . 2b) ☑ T	his action is non-final.		
3) Since this application is in condition for allow	vance except for formal ma	ters, prosecution as to the merits is	
closed in accordance with the practice unde	er Ex parte Quayle, 1935 C.	D. 11, 453 O.G. 213.	
Disposition of Claims			
4) ☐ Claim(s) 1-13 is/are pending in the application 4a) Of the above claim(s) is/are withd 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and	rawn from consideration.		
Application Papers			
9) ☐ The specification is objected to by the Example 10) ☑ The drawing(s) filed on 23 January 2004 is/a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the	re: a)⊠ accepted or b)⊡ he drawing(s) be held in abeya rection is required if the drawin	nce. See 37 CFR 1.85(a). g(s) is objected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for forei a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the papplication from the International Burd * See the attached detailed Office action for a light copies.	ents have been received. ents have been received in a riority documents have been eau (PCT Rule 17.2(a)).	Application No received in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892)		Summary (PTO-413)	
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date 		(s)/Mail Date Informal Patent Application (PTO-152) 	

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1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) The invention was described in (1) an application for patent, published under Section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

The following is a quotation of 35 U.S.C. § 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and

the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-13 are rejected under 35 U.S.C. 102(b) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Hosoi '974. Hosoi '974 (see particularly paragraphs 43, 44, 51, 58-62, 78-80, 113; Example 1; Figures 1 and 5) discloses phosphor crystals and a support wherein the crystals are in the shape of columns with diameters of 1-100 microns and voids that are less than 10 microns wide. The crystals are formed by vapor deposition of metal halide phosphor materials within the scope of Formula 3 of instant claim 4 as are the crystals of the instant claims. Example 1 of Hosoi discloses crystals of 8 microns aligned thickly. The diameters of the phosphor crystals and voids in Hosoi fall within the preferred ranges set forth on page 16 of applicants' specification. Therefore, the number of crystals in Hosoi would fall within the range of 50 to 4000 per 100 microns squared or it would at least be obvious to one skilled in the art to adjust the diameters of the crystals and voids in Hosoi within the preferred ranges.

2. Claims 1-13 are rejected under 35 U.S.C. 102(b) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as

obvious over Hosoi '050. Hosoi '050 (see particularly column 3, lines 20-50; column 2, lines 35-49; Example 1) discloses columns of phosphors on supports with densities of 85-97%. The phosphors include those of instant claim 4. Example 1 discloses phosphor crystals with diameters of 10 microns at 95% of the area for approximately 95 phosphor crystals per 100 microns squared. It would be obvious to one skilled in the art to adjust the diameters of the crystals and their densities in Hosoi within the disclosed density ranges of Hosoi which would provide numbers of crystals per unit area as required by the instant claims.

3. Claims 1-13 are rejected under 35 U.S.C. 102(a) and (e) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Morikawa et al. '529. Morikawa et al. '529 (see particularly paragraphs 9, 10, 16-26, 38, 39, 43-46, 51, 71-74) disclose gas phase growth of phosphor crystals in column form on a support. The diameters of the phosphor crystals in the Examples are 5 microns and spaces between crystals are disclosed as preferably being not more than 5 microns in Morikawa et al. so that the number of crystals per 100 microns squared is at least 100. Alternatively, it would at least be obvious to one skilled in the art to use preferred spacings of the crystals of less than 5 microns as disclosed in Morikawa et al. in the Examples with crystal diameters of 5 microns to obtain crystals per 100

microns squared of 100 or more.

Any inquiry concerning this communication should be directed to Mr. Schilling at telephone number (571) 272-1335.

RLSchilling:cdc

June 2, 2005

RICHARD L. SCHILLING PRIMARY EXAMINER
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